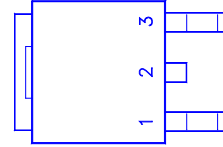
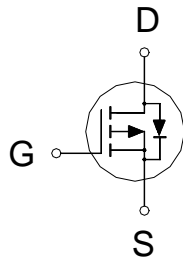




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-60V	90mΩ	-15A



1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25\text{ °C}$	I_D	-15	A
	$T_C = 100\text{ °C}$		-10	
Pulsed Drain Current ¹		I_{DM}	-50	
Avalanche Current		I_{AS}	-25	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	31	mJ
Power Dissipation	$T_C = 25\text{ °C}$	P_D	41	W
	$T_C = 100\text{ °C}$		16	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3	°C / W
Junction-to-Ambient	$R_{\theta JA}$		75	°C / W

¹Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ °C}$, Unless Otherwise Noted)

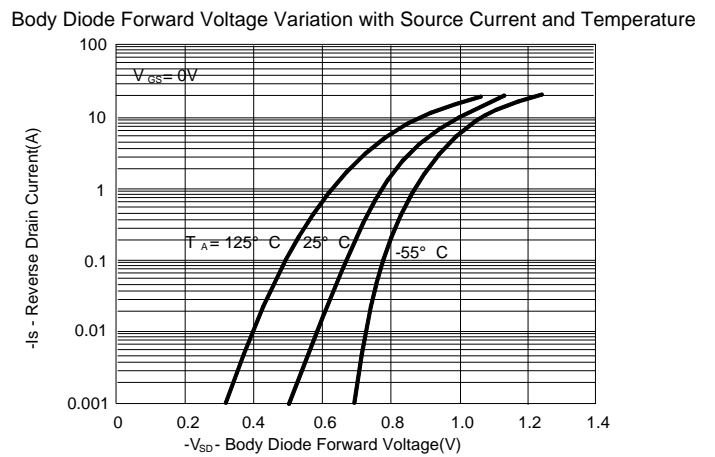
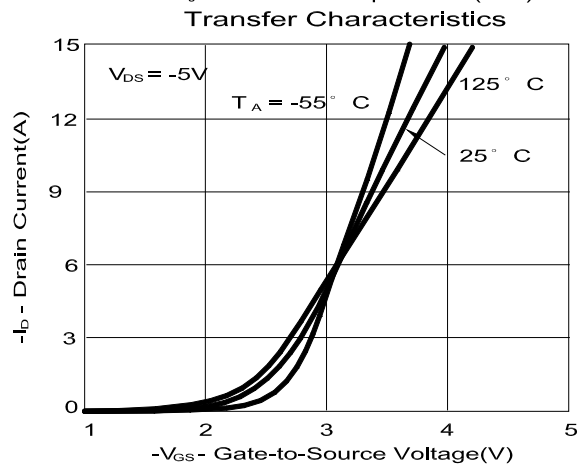
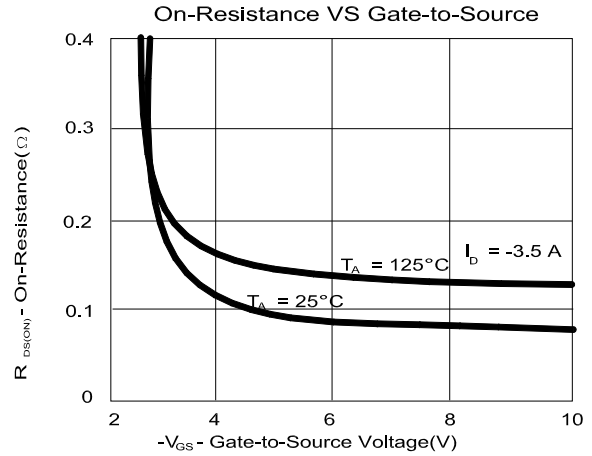
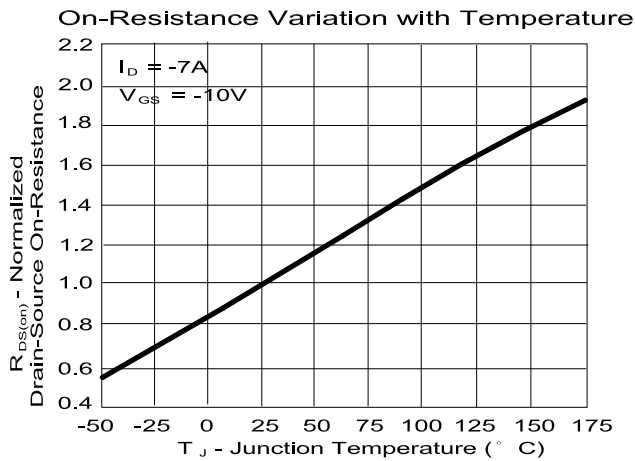
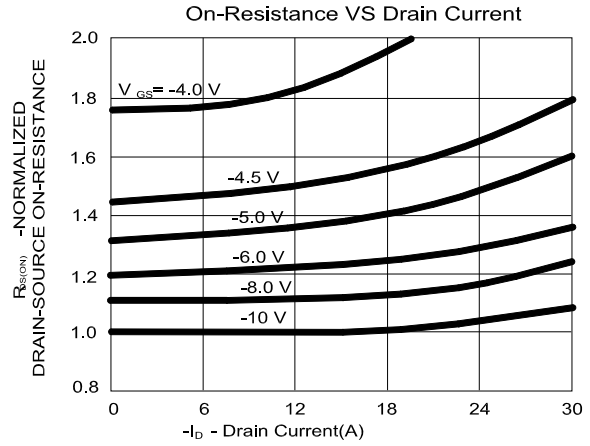
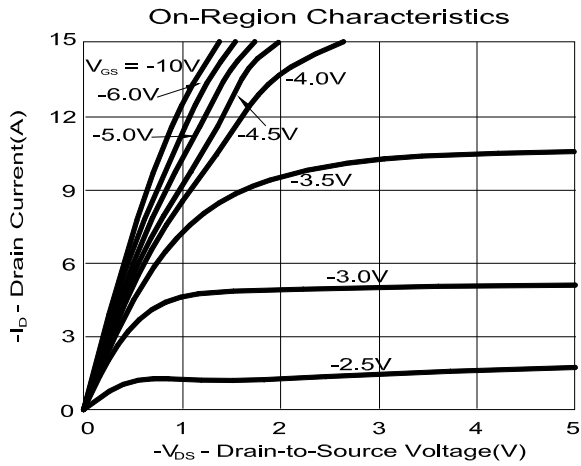
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.7	-3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			±250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -48V, V_{GS} = 0V$			1	μA
		$V_{DS} = -40V, V_{GS} = 0V, T_J = 125\text{ °C}$			10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = -5V, V_{GS} = -10V$	-50			A

Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = -4.5V, I_D = -6A$	100	135	$m\Omega$
		$V_{GS} = -10V, I_D = -7A$	70	90	
Forward Transconductance ¹	g_{fs}	$V_{DS} = -10V, I_D = -7A$	9		S
DYNAMIC					
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -25V, f = 1MHz$	1130		pF
Output Capacitance	C_{oss}		95		
Reverse Transfer Capacitance	C_{rss}		65		
Total Gate Charge ²	Q_g	$V_{DS} = -48V, V_{GS} = -10V, I_D = -7A$	23.1		nC
Gate-Source Charge ²	Q_{gs}		6.8		
Gate-Drain Charge ²	Q_{gd}		3.8		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = -20V, I_D \cong -1A, V_{GS} = -10V, R_{GS} = 6\Omega$	7		nS
Rise Time ²	t_r		10		
Turn-Off Delay Time ²	$t_{d(off)}$		19		
Fall Time ²	t_f		12		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ C$)					
Continuous Current ³	I_S			-15	A
Forward Voltage ¹	V_{SD}	$I_F = -7A, V_{GS} = 0V$		-1	V
Reverse Recovery Time	t_{rr}	$I_F = -7A, di_F/dt = 100A / \mu S$	37		nS
Reverse Recovery Charge	Q_{rr}		53		nC

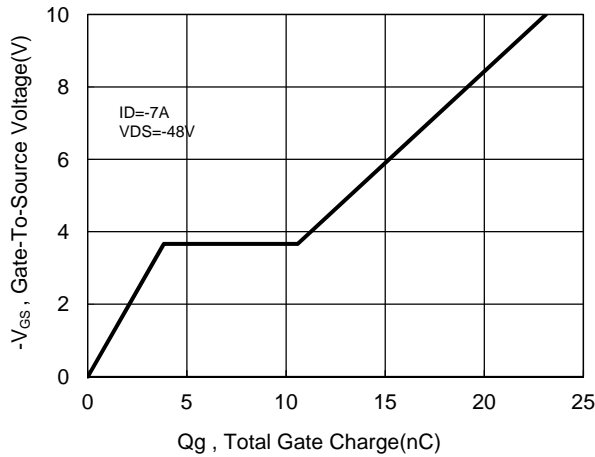
¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

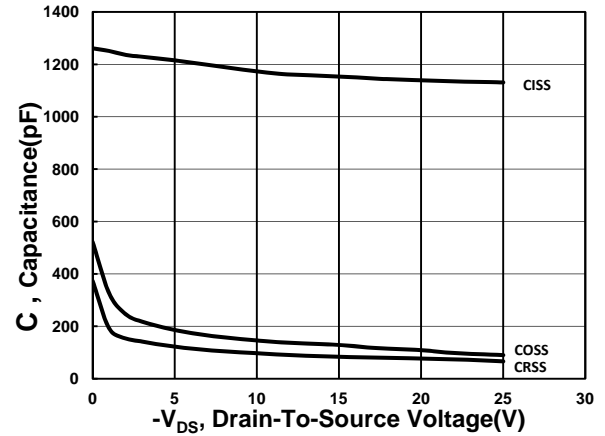
³Pulse width limited by maximum junction temperature.



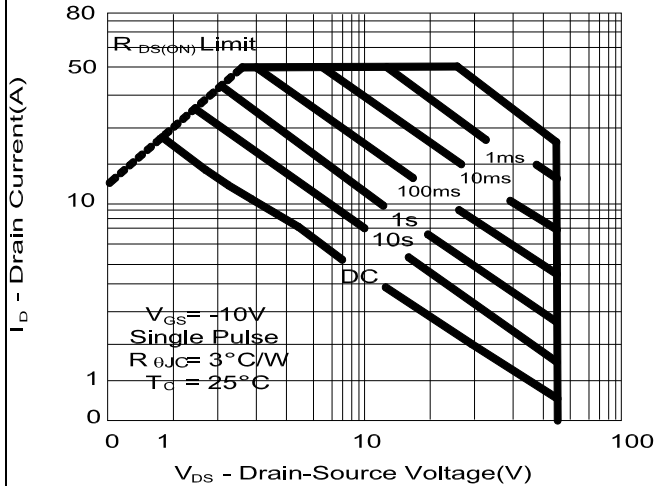
Gate charge Characteristics



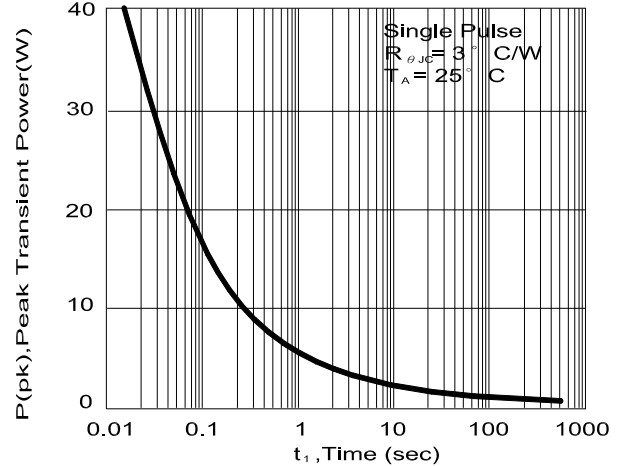
Capacitance Characteristics



Maximum Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

